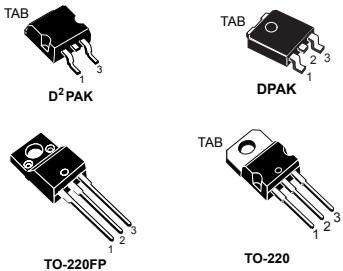


8 A, 600 V short-circuit rugged IGBT



## Features

- Lower on voltage drop ( $V_{CE(sat)}$ )
- Lower  $C_{res}$  /  $C_{ies}$  ratio (no cross-conduction susceptibility)
- Very soft ultra fast recovery antiparallel diode
- Short-circuit withstand time 10  $\mu$ s

## Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies
- Motor drives

## Description

These devices are very fast IGBTs developed using advanced PowerMESH technology. This process guarantees an excellent trade-off between switching performance and low on-state behavior. These devices are well-suited for resonant or soft-switching applications.

### Product status links

<a href="#">STGB8NC60KD</a>
<a href="#">STGD8NC60KD</a>
<a href="#">STGF8NC60KD</a>
<a href="#">STGP8NC60KD</a>



NG1E3C2T

Product status links
<a href="#">STGB8NC60KD</a>
<a href="#">STGD8NC60KD</a>
<a href="#">STGF8NC60KD</a>
<a href="#">STGP8NC60KD</a>

## 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value			Unit
		D <sup>2</sup> PAK, TO-220	DPAK	TO-220FP	
V <sub>CES</sub>	Collector-emitter voltage (V <sub>GE</sub> = 0 V)	600			V
I <sub>C</sub> <sup>(1)</sup>	Continuous collector current at T <sub>C</sub> = 25 °C	15	7		A
	Continuous collector current at T <sub>C</sub> = 100 °C	8	4		
I <sub>CL</sub> <sup>(2)</sup>	Turn-off latching current	30			A
I <sub>CP</sub> <sup>(3)</sup>	Pulsed collector current	30			A
V <sub>GE</sub>	Gate-emitter voltage	±20			V
I <sub>F</sub>	Diode RMS forward current at T <sub>C</sub> = 25 °C	7			A
I <sub>FSM</sub>	Surge non repetitive forward current t <sub>p</sub> = 10 ms sinusoidal	20			A
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T <sub>C</sub> = 25 °C)			2.5	kV
t <sub>scw</sub>	Short-circuit withstand time V <sub>CE</sub> = 0.5, V <sub>CES</sub> , T <sub>J</sub> = 125 °C, R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 12 V	10			μs
P <sub>TOT</sub>	Total power dissipation at T <sub>C</sub> = 25 °C	65	62	24	W
T <sub>stg</sub>	Storage temperature range	-55 to 150			°C
T <sub>J</sub>	Operating junction temperature range				°C

1. Calculated according to the iterative formula:  $I_C(T_C) = \frac{T_J(\max) - T_C}{R_{thJC} \times V_{CE(sat)(\max)}(T_J(\max), I_C(T_C))}$

2. V<sub>clamp</sub> = 80% V<sub>CES</sub>. T<sub>J</sub> = 150 °C, R<sub>G</sub> = 10 Ω, V<sub>GE</sub> = 15 V.

3. Pulse width limited by maximum junction temperature and turn-off within RBSOA.

**Table 2. Thermal data**

Symbol	Parameter	Value			Unit
		D <sup>2</sup> PAK, TO-220	DPAK	TO-220FP	
R <sub>thJC</sub>	Thermal resistance, junction-to-case IGBT	1.9	2.0	5.1	°C/W
	Thermal resistance, junction-to-case diode	4	4.5	7	
R <sub>thJA</sub>	Thermal resistance, junction-to-ambient	62.5	100	62.5	°C/W

## 2 Electrical characteristics

$T_C = 25^\circ\text{C}$  unless otherwise specified

**Table 3. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{CES}}$	Collector-emitter breakdown voltage	$V_{GE} = 0 \text{ V}, I_C = 1 \text{ mA}$	600			V
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_{GE} = 15 \text{ V}, I_C = 3 \text{ A}$		2.2	2.75	V
		$V_{GE} = 15 \text{ V}, I_C = 3 \text{ A}, T_J = 125^\circ\text{C}$		1.8		
$V_{GE(\text{th})}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 250 \mu\text{A}$	4.5		6.5	V
$I_{CES}$	Collector cut-off current	$V_{GE} = 0 \text{ V}, V_{CE} = 600 \text{ V}$			0.15	mA
		$V_{GE} = 0 \text{ V}, V_{CE} = 600 \text{ V}, T_J = 125^\circ\text{C}$ (1)			1	
$I_{GES}$	Gate-emitter leakage current	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100$	nA
$g_{fs}$ (2)	Forward transconductance	$V_{CE} = 15 \text{ V}, I_C = 3 \text{ A}$		1.9		S

1. Specified by design, not tested in production.

2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25 \text{ V}, f = 1 \text{ MHz}, V_{GE} = 0 \text{ V}$	-	380	-	pF
$C_{oes}$	Output capacitance		-	46	-	pF
$C_{res}$	Reverse transfer capacitance		-	8.5	-	pF
$Q_g$	Total gate charge	$V_{CC} = 390 \text{ V}, I_C = 3 \text{ A}, V_{GE} = 0 \text{ to } 15 \text{ V}$ (see Figure 19. Gate charge test circuit)	-	19	-	nC
$Q_{ge}$	Gate-emitter charge		-	5	-	nC
$Q_{gc}$	Gate-collector charge		-	9	-	nC

**Table 5. Switching on/off (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390 \text{ V}, I_C = 3 \text{ A}, R_G = 10 \Omega, V_{GE} = 15 \text{ V}$ (see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	17	-	ns
$t_r$	Current rise time		-	6	-	ns
$(di/dt)_{on}$	Turn-on current slope	$V_{CC} = 390 \text{ V}, I_C = 3 \text{ A}, R_G = 10 \Omega, V_{GE} = 15 \text{ V}, T_J = 125^\circ\text{C}$ (see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	655	-	A/ $\mu$ s
$t_{d(on)}$	Turn-on delay time		-	16.5	-	ns
$t_r$	Current rise time		-	6.5	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	575	-	A/ $\mu$ s
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390 \text{ V}, I_C = 3 \text{ A}, R_G = 10 \Omega, V_{GE} = 15 \text{ V}$ (see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	33	-	ns
$t_{d(off)}$	Turn-off delay time		-	72	-	ns
$t_f$	Current fall time		-	82	-	ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390 \text{ V}, I_C = 3 \text{ A}, R_G = 10 \Omega, V_{GE} = 15 \text{ V}, T_J = 125^\circ\text{C}$ (see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	60	-	ns
$t_{d(off)}$	Turn-off delay time		-	106	-	ns
$t_f$	Current fall time		-	136	-	ns

**Table 6. Switching energy (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CE} = 390 \text{ V}, I_C = 3 \text{ A}, R_G = 10 \Omega, V_{GE} = 15 \text{ V}$ (see Figure 17. Test circuit for inductive load switching)	-	55	-	$\mu$ J
$E_{off}^{(2)}$	Turn-off switching energy		-	85	-	$\mu$ J
$E_{ts}$	Total switching energy	$V_{CE} = 390 \text{ V}, I_C = 3 \text{ A}, R_G = 10 \Omega, V_{GE} = 15 \text{ V}, T_J = 125^\circ\text{C}$ (see Figure 17. Test circuit for inductive load switching)	-	140	-	$\mu$ J
$E_{on}^{(1)}$	Turn-on switching energy		-	87	-	$\mu$ J
$E_{off}^{(2)}$	Turn-off switching energy		-	162	-	$\mu$ J
$E_{ts}$	Total switching energy		-	249	-	$\mu$ J

1. Including the reverse recovery of the diode.

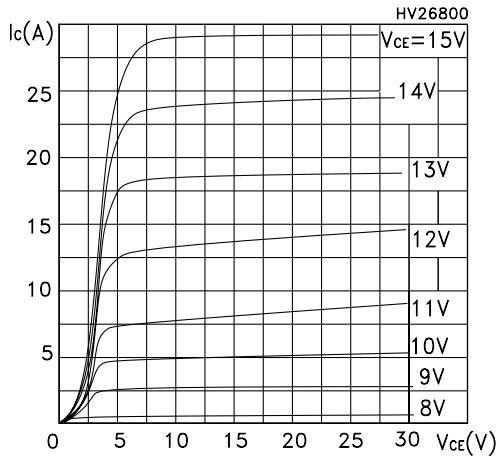
2. Including the tail of the collector current.

**Table 7. Diode switching characteristics (inductive load)**

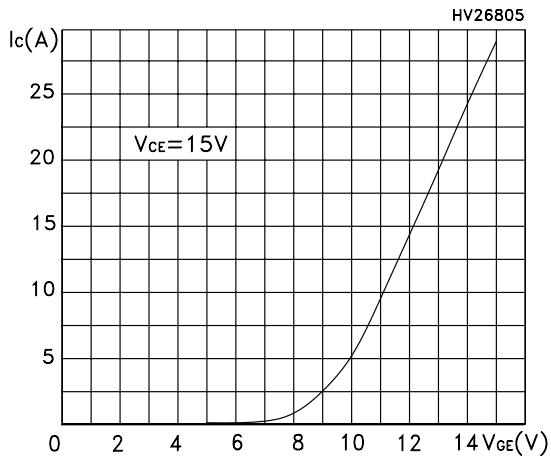
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>F</sub>	Forward on-voltage	I <sub>F</sub> = 3A	-	1.6	2.1	V
		I <sub>F</sub> = 3 A, T <sub>J</sub> =125 °C	-	1.3		
t <sub>rr</sub>	Reverse recovery time	I <sub>F</sub> = 3 A, V <sub>R</sub> = 30 V, di/dt = 100 A/μs	-	23.5		ns
Q <sub>rr</sub>	Reverse recovery charge	(see Figure 18. Diode reverse recovery waveform)	-	16.5		nC
I <sub>rrm</sub>	Reverse recovery current		-	1.4		A
t <sub>rr</sub>	Reverse recovery time	I <sub>F</sub> = 3 A, V <sub>R</sub> = 30 V, di/dt = 100 A/μs,	-	39		ns
Q <sub>rr</sub>	Reverse recovery charge	T <sub>J</sub> = 125 °C (see Figure 18. Diode reverse recovery waveform)	-	39		nC
I <sub>rr</sub>	Reverse recovery current		-	2		A

## 2.1 Electrical characteristics (curves)

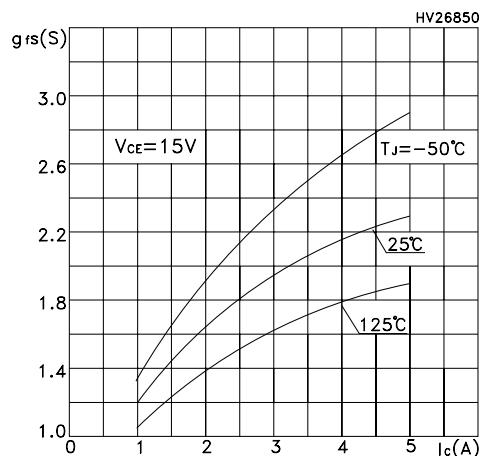
**Figure 1. Typical output characteristics**



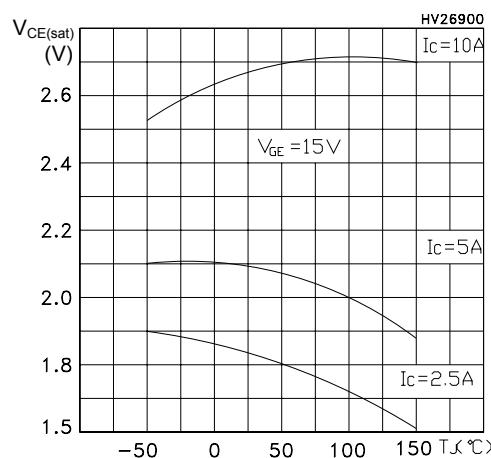
**Figure 2. Typical transfer characteristics**



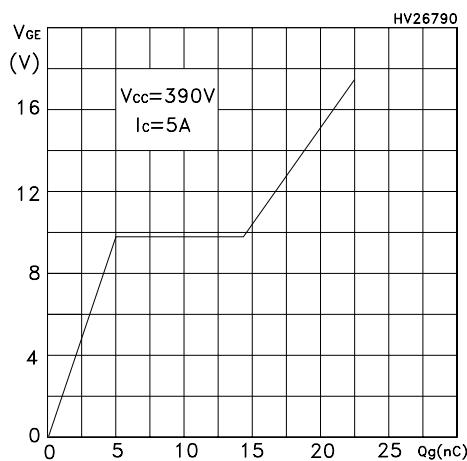
**Figure 3. Typical transconductance characteristics**



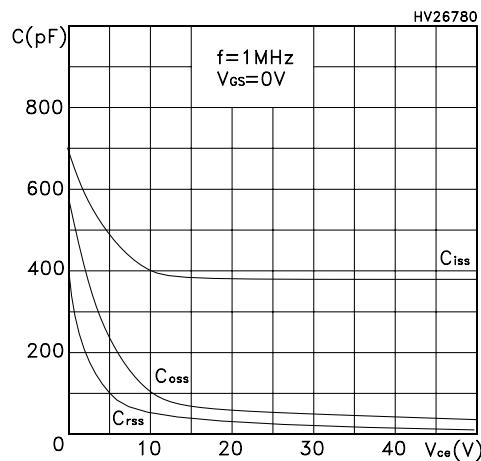
**Figure 4. Typical collector-emitter on voltage vs temperature**

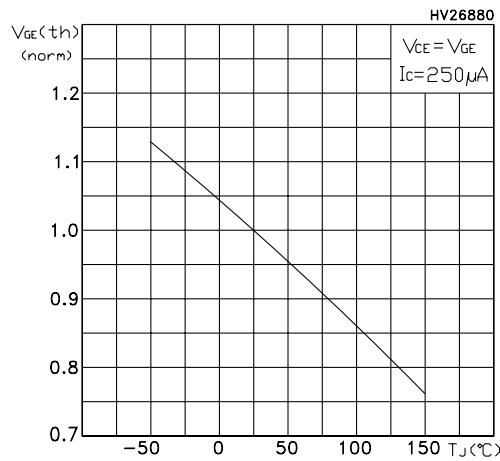
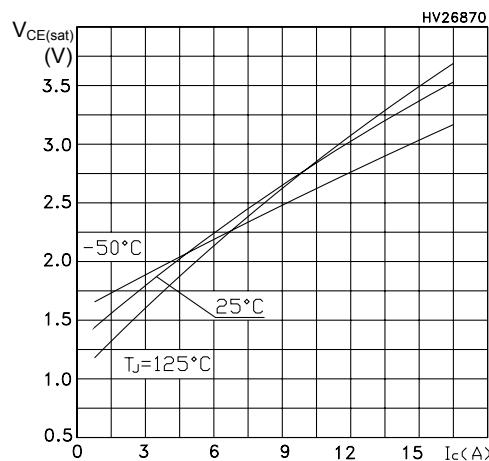
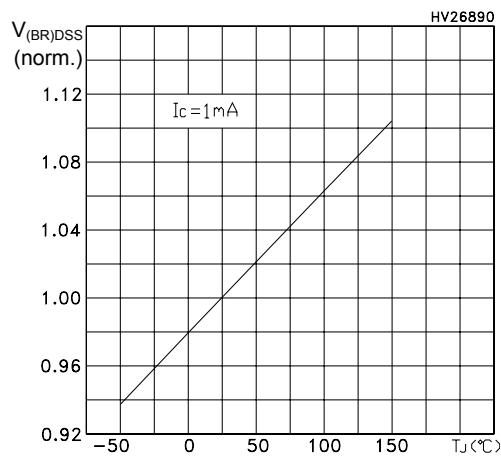
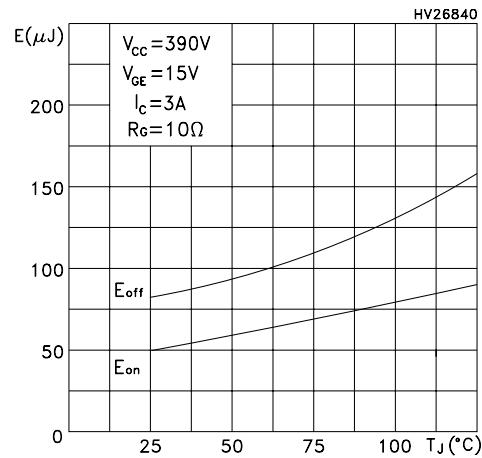
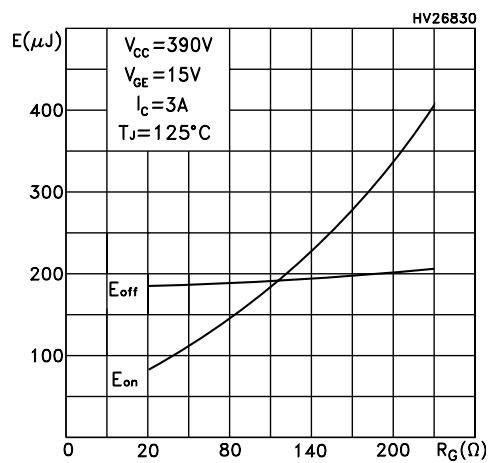
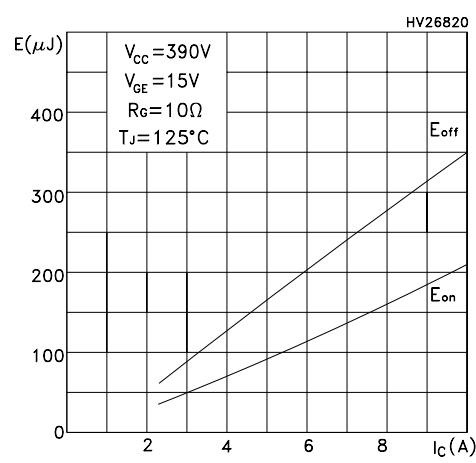


**Figure 5. Typical gate charge characteristics**

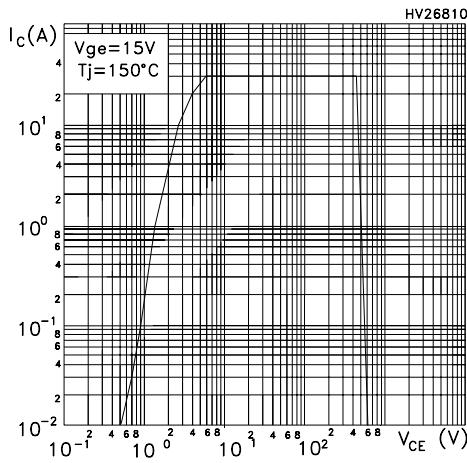


**Figure 6. Typical capacitance characteristics**

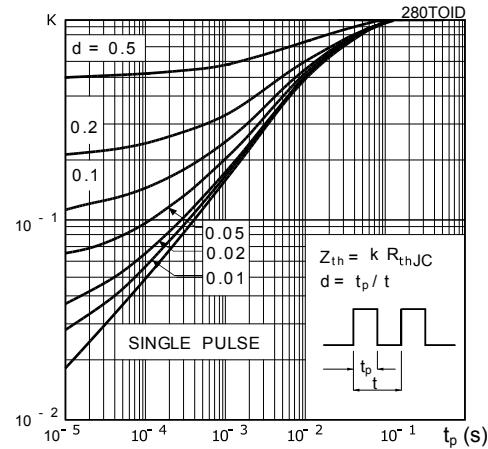


**Figure 7. Normalized gate threshold vs temperature**

**Figure 8. Typical collector-emitter on voltage vs collector current**

**Figure 9. Normalized breakdown voltage vs temperature**

**Figure 10. Typical switching energy vs temperature**

**Figure 11. Typical switching energy vs gate resistance**

**Figure 12. Typical switching energy vs collector current**


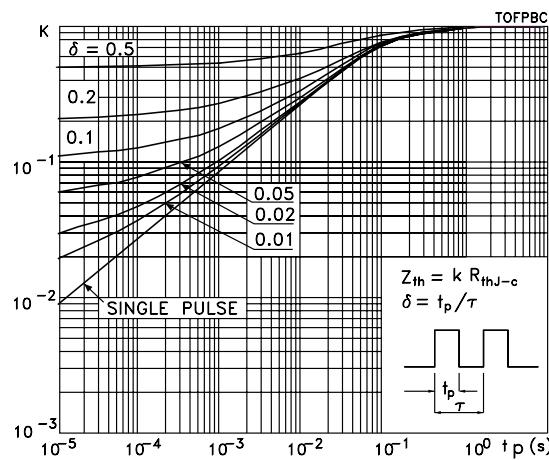
**Figure 13. Reverse bias safe operating area**



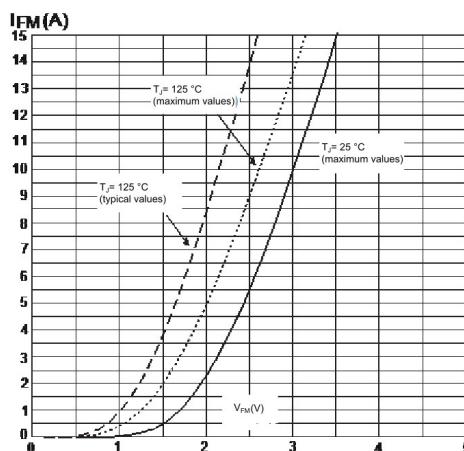
**Figure 14. Normalized transient thermal impedance for D<sup>2</sup>PAK, DPAK and TO-220**



**Figure 15. Normalized transient thermal impedance for TO-220FP**

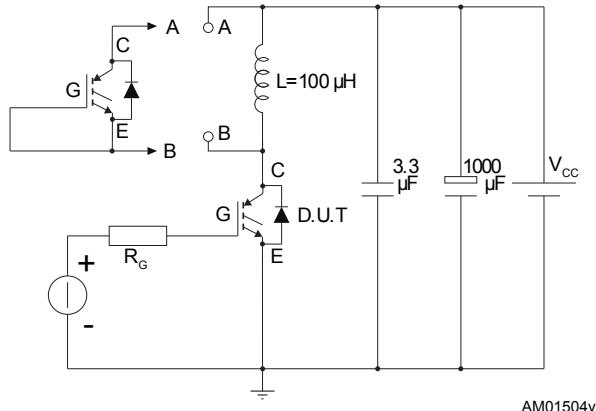


**Figure 16. Typical emitter-collector diode characteristics**



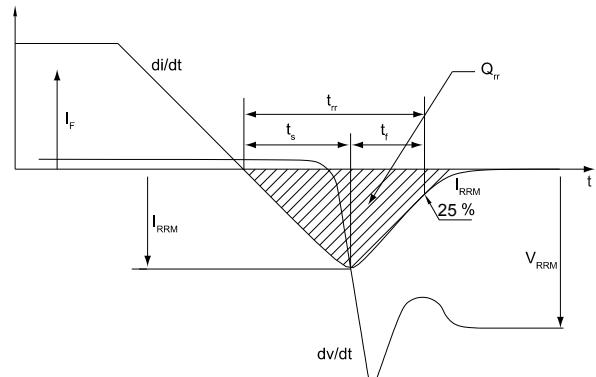
### 3 Test circuits

**Figure 17. Test circuit for inductive load switching**



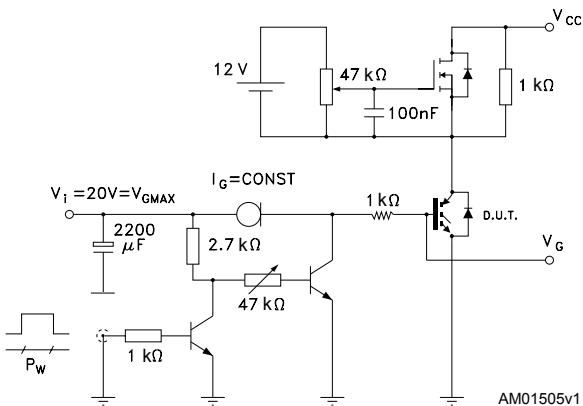
AM01504v1

**Figure 18. Diode reverse recovery waveform**



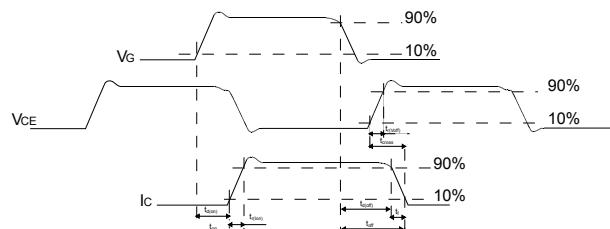
AM01507v1

**Figure 19. Gate charge test circuit**



AM01505v1

**Figure 20. Switching waveform**



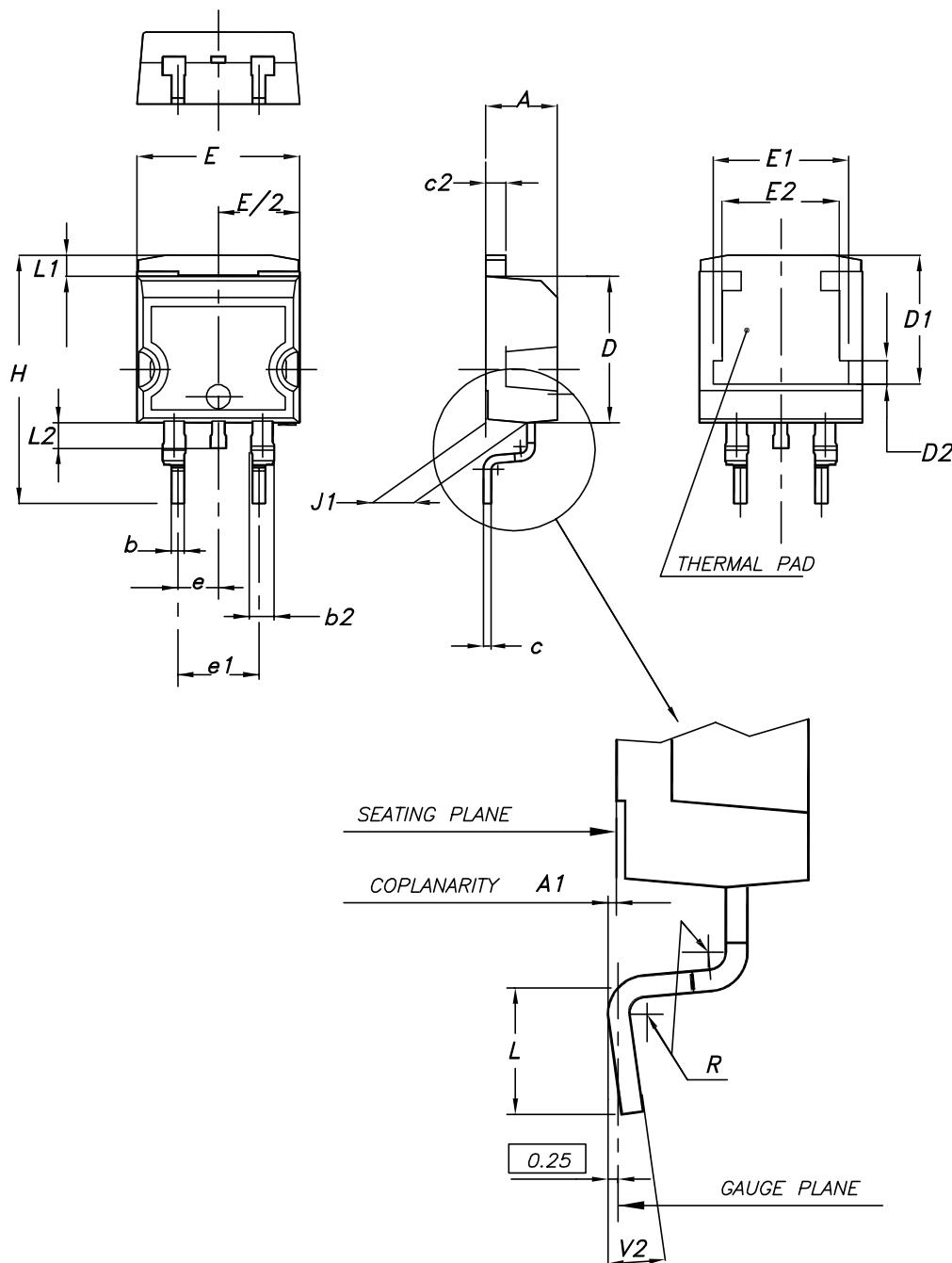
AM01506v1

## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 D<sup>2</sup>PAK (TO-263) package information

Figure 21. D<sup>2</sup>PAK (TO-263) type A package outline

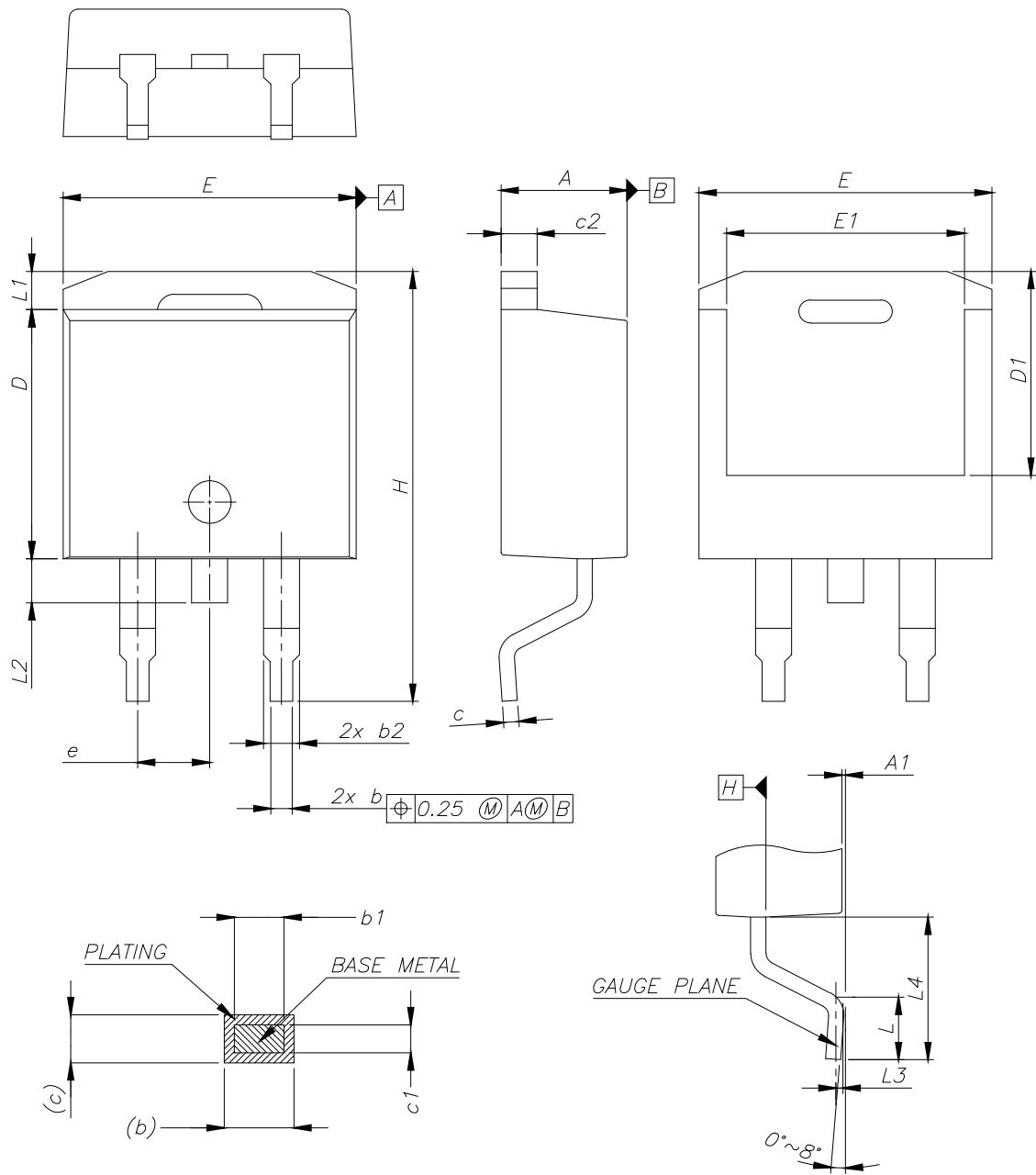


0079457\_26

Table 8. D<sup>2</sup>PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

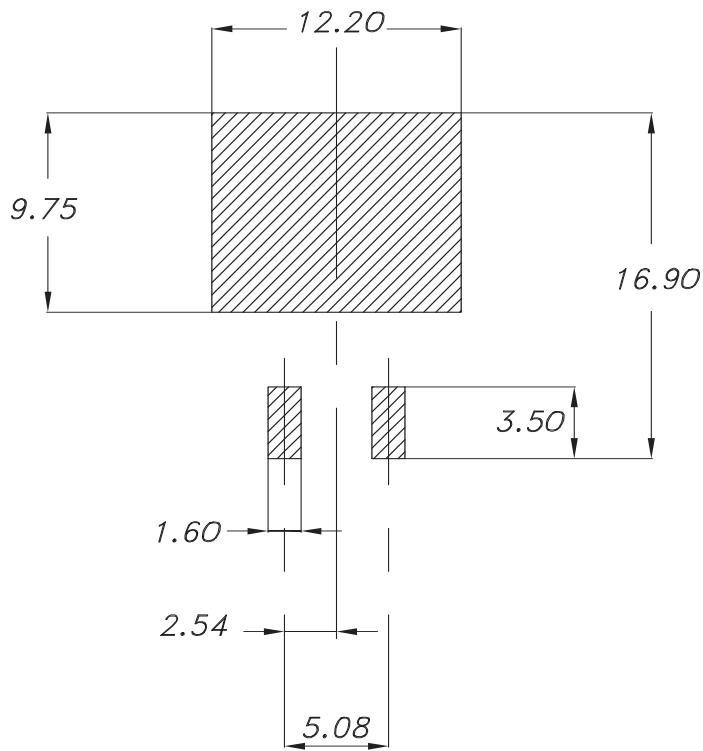
**Figure 22. D<sup>2</sup>PAK (TO-263) type B package outline**



0079457\_26\_B

**Table 9. D<sup>2</sup>PAK (TO-263) type B mechanical data**

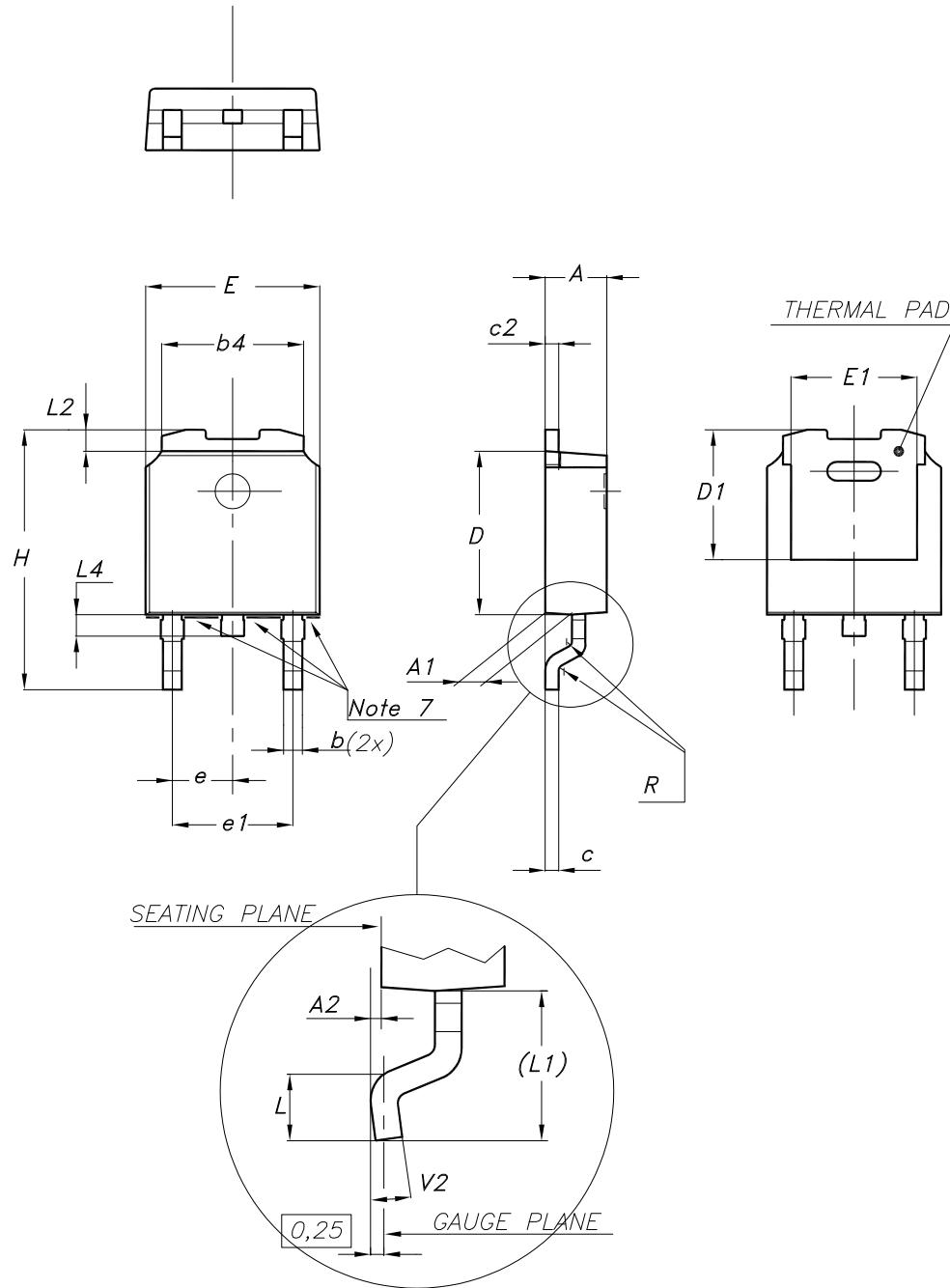
Dim.	mm		
	Min.	Typ.	Max.
A	4.36		4.56
A1	0		0.25
b	0.70		0.90
b1	0.51		0.89
b2	1.17		1.37
c	0.38		0.694
c1	0.38		0.534
c2	1.19		1.34
D	8.60		9.00
D1	6.90		7.50
E	10.15		10.55
E1	8.10		8.70
e	2.54 BSC		
H	15.00		15.60
L	1.90		2.50
L1			1.65
L2			1.78
L3		0.25	
L4	4.78		5.28

**Figure 23. D<sup>2</sup>PAK (TO-263) recommended footprint (dimensions are in mm)**


0079457\_Rev26\_footprint

## 4.2 DPAK (TO-252) type A package information

Figure 24. DPAK (TO-252) type A package outline



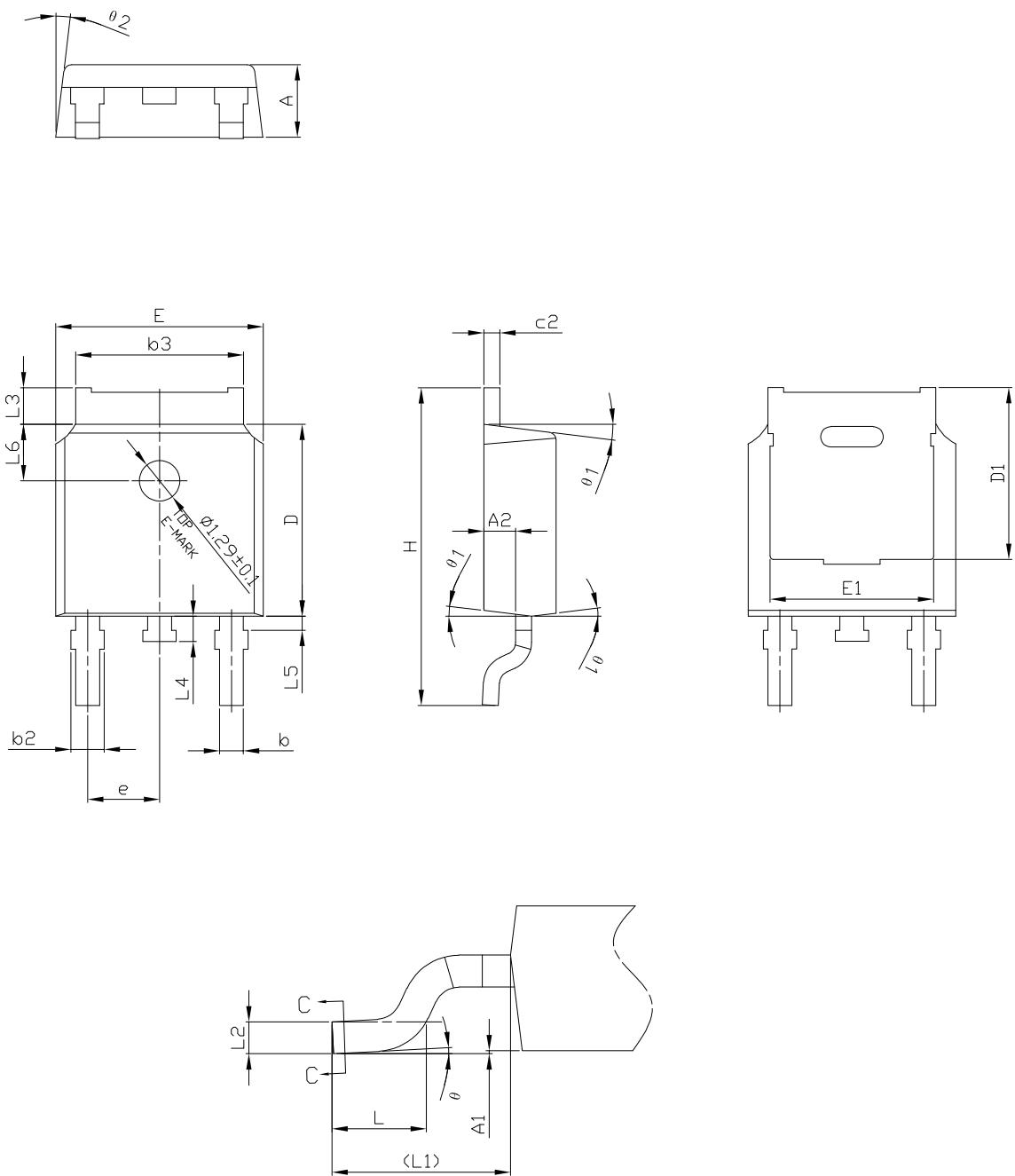
0068772\_A\_34

Table 10. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

#### 4.3 DPAK (TO-252) type C3 package information

**Figure 25. DPAK (TO-252) type C3 package outline**

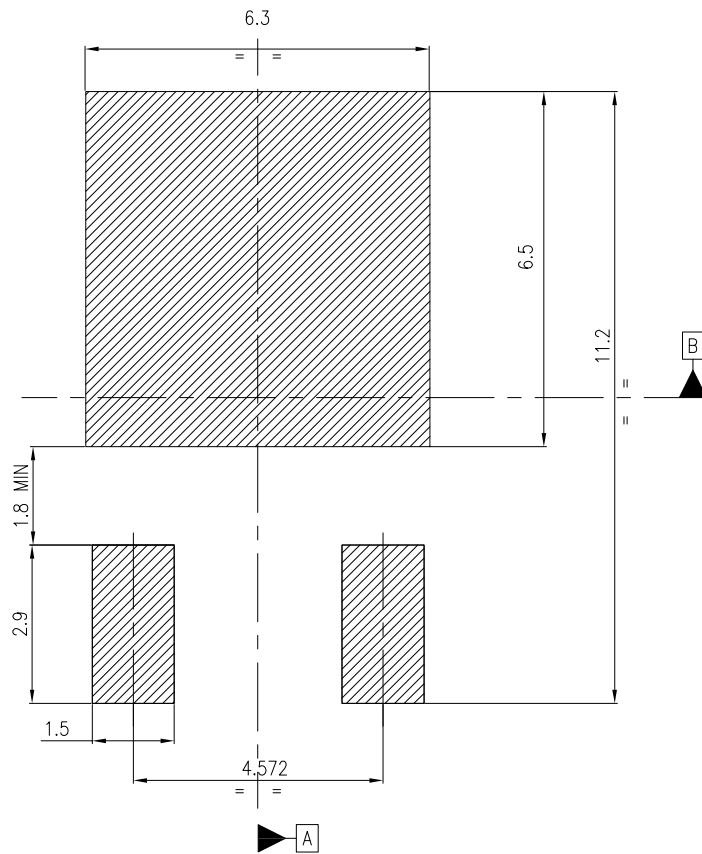


0068772\_type-C3\_rev34

Table 11. DPAK (TO-252) type C3 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.00		0.10
A2	0.90	1.01	1.10
b	0.72		0.85
b2	0.72		1.10
b3	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.20	5.45	5.70
E	6.50	6.60	6.70
E1	5.00	5.20	5.40
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.51 BSC		
L3	0.90		1.25
L4	0.60	0.80	1.00
L5	0.15		0.75
L6	1.80 REF		
θ	0°		8°
θ1	5°	7°	9°
θ2	5°	7°	9°

**Figure 26. DPAK (TO-252) recommended footprint (dimensions are in mm)**



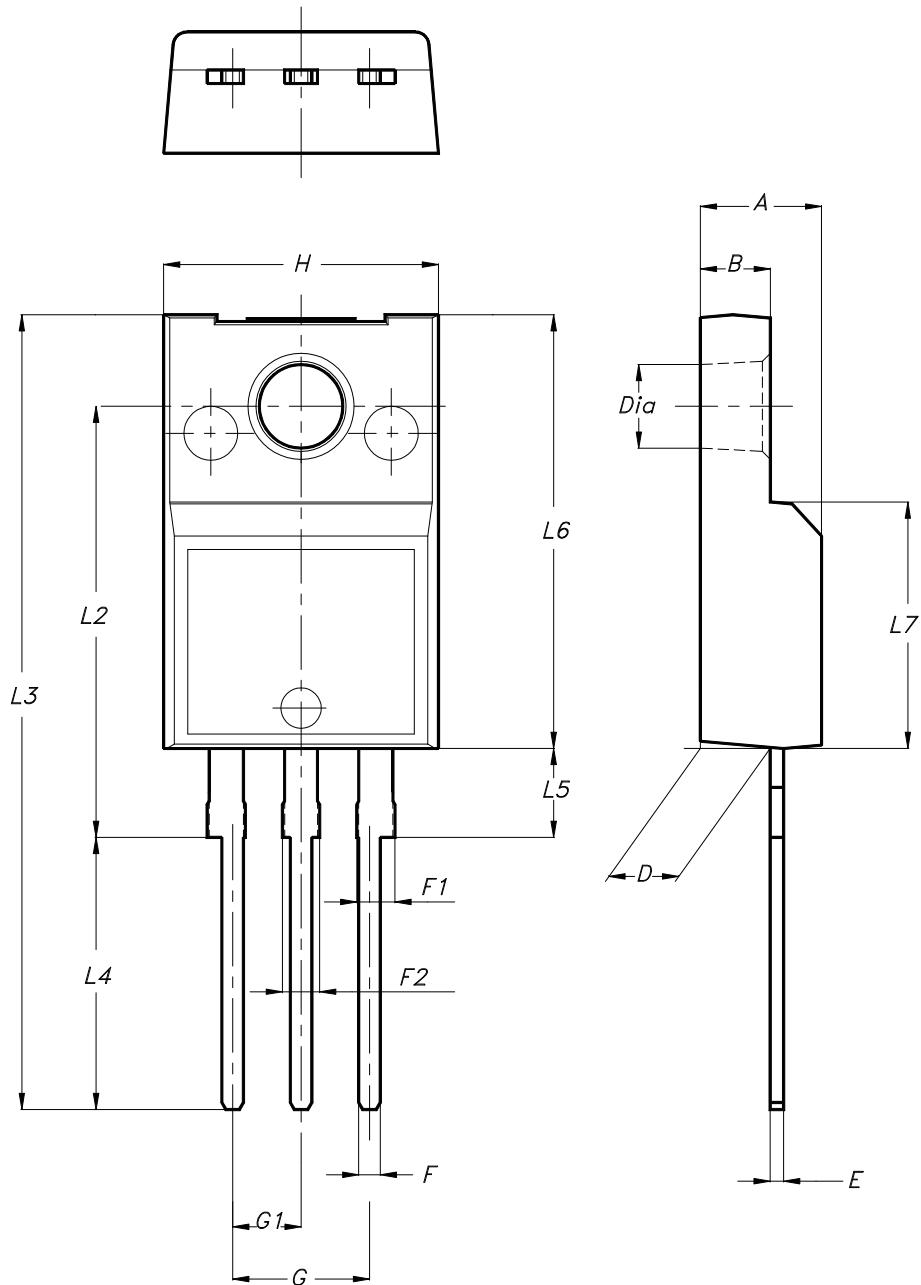
Notes:

- 1) This footprint is able to ensure insulation up to 630 Vrms (according to CEI IEC 664-1)
- 2) The device must be positioned within  $\Phi 0.05$  A B

FP\_0068772\_34

#### 4.4 TO-220FP type B package information

Figure 27. TO-220FP type B package outline



7012510\_B\_rev.14



Table 12. TO-220FP type B package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

## 4.5 TO-220 type A package information

Figure 28. TO-220 type A package outline

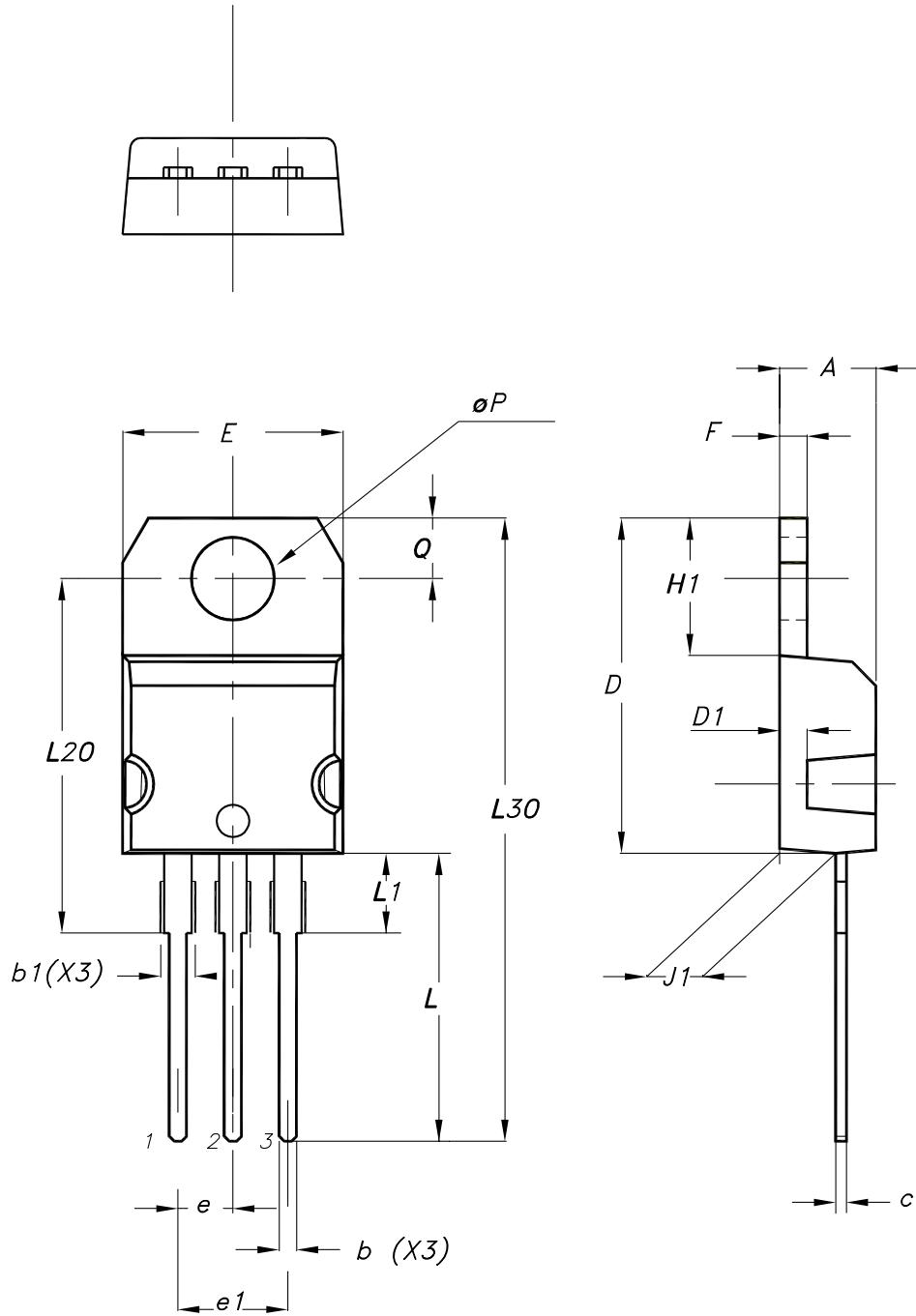
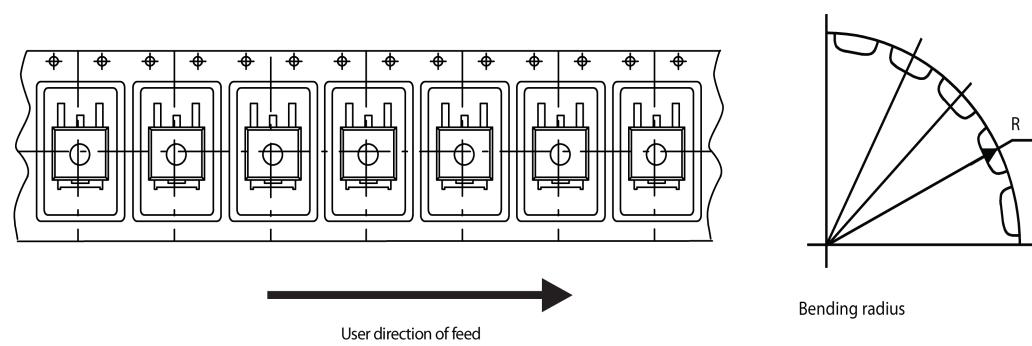
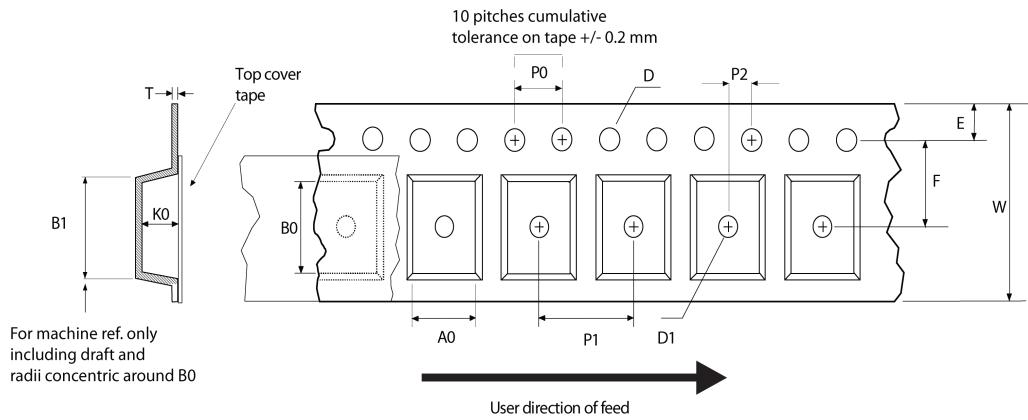


Table 13. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

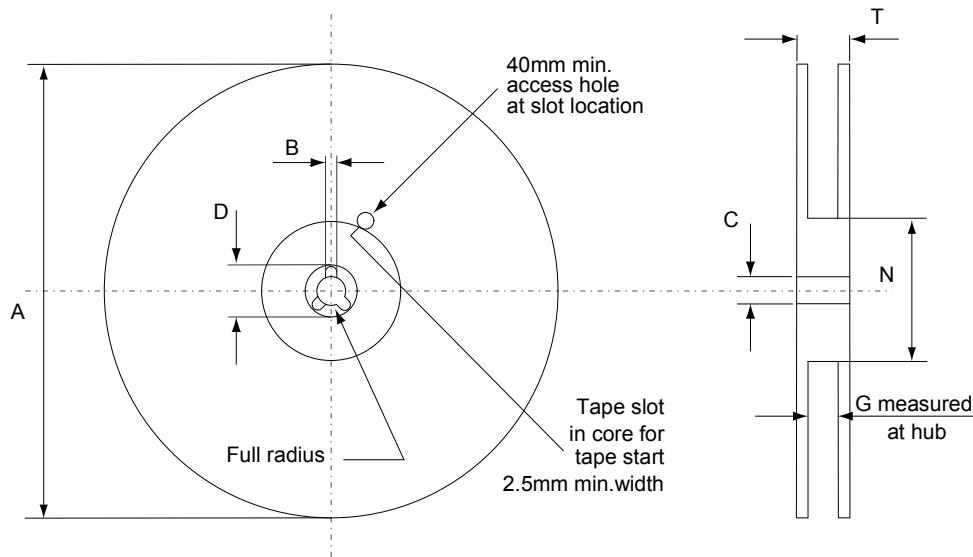
## 4.6 D<sup>2</sup>PAK type A packing information

**Figure 29. D<sup>2</sup>PAK tape outline**



Bending radius

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Figure 30. D<sup>2</sup>PAK reel outline


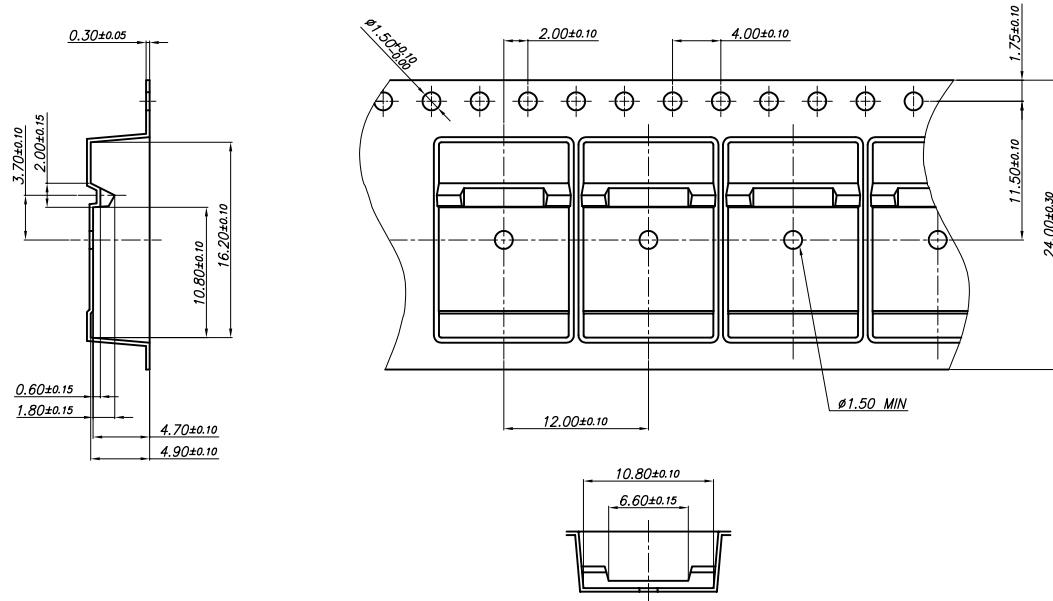
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Table 14. D<sup>2</sup>PAK tape and reel mechanical data

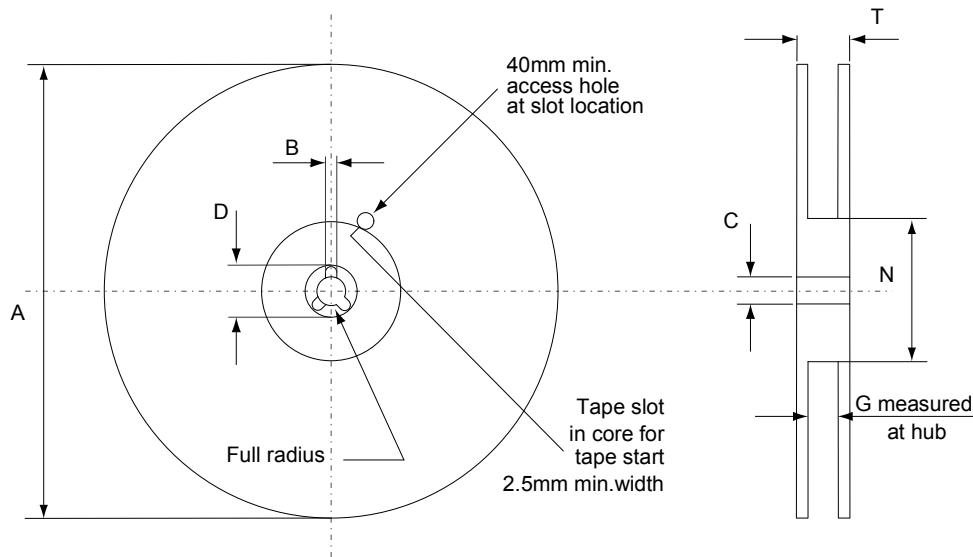
Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

## 4.7 D<sup>2</sup>PAK type B packing information

**Figure 31. D<sup>2</sup>PAK type B tape outline**



**Figure 32. D<sup>2</sup>PAK type B reel outline**

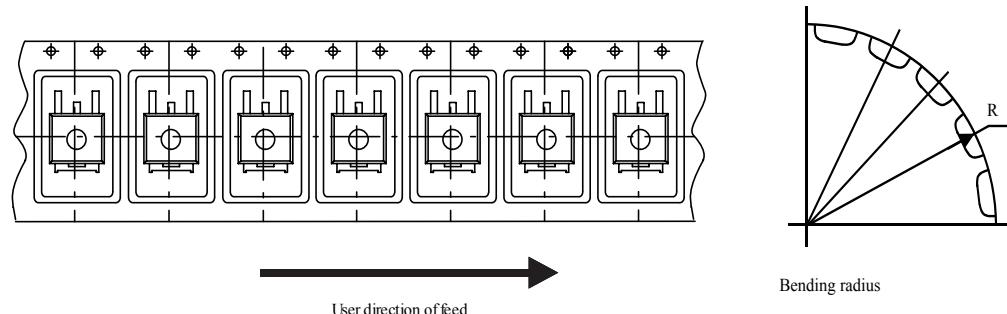
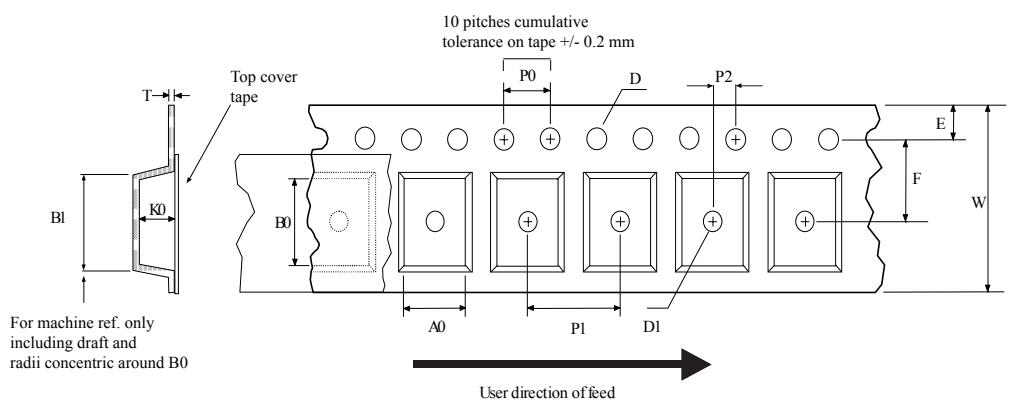


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**Table 15. D<sup>2</sup>PAK type B reel mechanical data**

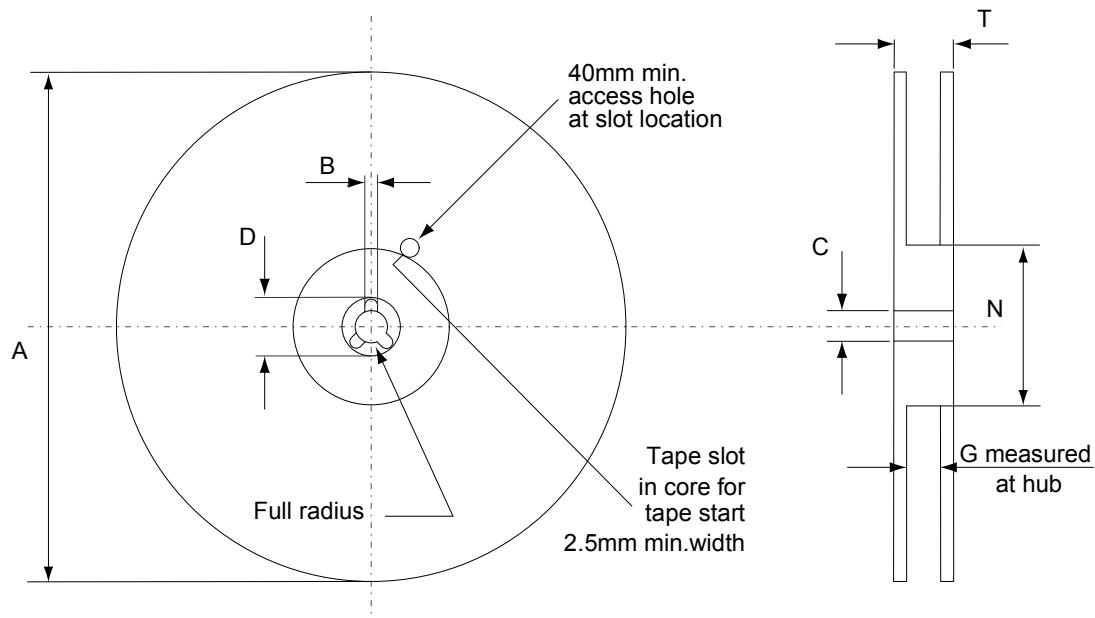
Dim.	mm	
	Min.	Max.
A		330
B	1.5	
C	12.8	13.2
D	20.2	
G	24.4	26.4
N	100	
T		30.4

#### 4.8 DPAK (TO-252) packing information

**Figure 33. DPAK (TO-252) tape outline**


Bending radius

AM08852v1

**Figure 34. DPAK (TO-252) reel outline**


AM06038v1

**Table 16. DPAK (TO-252) tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			



## 5 Ordering information

**Table 17. Order codes**

Order codes	Marking	Package	Packing
STGB8NC60KD	GB8NC60KD	D <sup>2</sup> PAK	Tape and reel
STGD8NC60KD	GD8NC60KD	DPAK	
STGF8NC60KD	GF8NC60KD	TO-220FP	Tube
STGP8NC60KD	GP8NC60KD	TO-220	

## Revision history

**Table 18. Document revision history**

Date	Revision	Changes
02-Oct-2007	1	First release.
01-Apr-2008	2	Updated <i>Figure 14</i> and <i>Figure 17</i>
09-Jun-2023	3	Updated the entire <a href="#">Section 4 Package information</a> . Minor text changes.

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